

CONTENTS

Preface	xv
Acknowledgements	xix
About the author(s)	xxi
About the book	xxiii
Introduction	xxv
1 Semiconductors and heterostructures	1
1.1 The mechanics of waves	1
1.2 Crystal structure	3
1.3 The effective mass approximation	5
1.4 Band theory	6
1.5 Heterojunctions	7
1.6 Heterostructures	8
1.7 The envelope function approximation	11
1.8 The reciprocal lattice	11
2 Solutions to Schrödinger's equation	17
2.1 The infinite well	17

vii

2.2	In-plane dispersion	20
2.3	Density of states	23
2.4	Subband populations	26
2.5	Finite well with constant mass	29
2.6	Effective mass mismatch at heterojunctions	34
2.7	The infinite barrier height and mass limits	36
2.8	Hermiticity and the kinetic energy operator	38
2.9	Alternative kinetic energy operators	40
2.10	Extension to multiple-well systems	41
2.11	The asymmetric single quantum well	44
2.12	Addition of an electric field	45
2.13	The infinite superlattice	48
2.14	The single barrier	54
2.15	The double barrier	56
2.16	Extension to include electric field	63
2.17	Magnetic fields and Landau quantisation	63
2.18	In summary	65
3	Numerical solutions	67
3.1	Shooting method	67
3.2	Generalized initial conditions	70
3.3	Practical implementation of the shooting method	72
3.4	Heterojunction boundary conditions	75
3.5	The parabolic potential well	76
3.6	The Pöschl–Teller potential hole	79
3.7	Convergence tests	81
3.8	Extension to variable effective mass	82
3.9	The double quantum well	85
3.10	Multiple quantum wells and finite superlattices	87
3.11	Addition of electric field	89
3.12	Quantum confined Stark effect	89
3.13	Field-induced anti-crossings	90
3.14	Symmetry and selection rules	91
3.15	The Heisenberg uncertainty principle	92
3.16	Extension to include band non-parabolicity	95
3.17	Poisson’s equation	98
3.18	Self-consistent Schrödinger–Poisson solution	102
3.19	Computational implementation	104
3.20	Modulation doping	105
3.21	The high-electron-mobility transistor	105

3.22	Band filling	107
4	Diffusion	109
4.1	Introduction	109
4.2	Theory	111
4.3	Boundary conditions	113
4.4	Convergence tests	113
4.5	Constant diffusion coefficients	115
4.6	Concentration dependent diffusion coefficient	117
4.7	Depth dependent diffusion coefficient	118
4.8	Time dependent diffusion coefficient	121
4.9	δ -doped quantum wells	122
4.10	Extension to higher dimensions	125
5	Impurities	127
5.1	Donors and acceptors in bulk material	127
5.2	Binding energy in a heterostructure	130
5.3	Two-dimensional trial wave function	135
5.4	Three-dimensional trial wave function	141
5.5	Variable-symmetry trial wave function	148
5.6	Inclusion of a central cell correction	155
5.7	Special considerations for acceptors	156
5.8	Effective mass and dielectric mismatch	156
5.9	Band non-parabolicity	157
5.10	Excited states	157
5.11	Application to spin-flip Raman spectroscopy	158
5.12	Alternative approach to excited impurity states	163
5.13	The ground state	164
5.14	Position dependence	166
5.15	Excited states	167
5.16	Impurity occupancy statistics	170
6	Excitons	175
6.1	Excitons in bulk	175
6.2	Excitons in heterostructures	177
6.3	Exciton binding energies	177
6.4	1s exciton	183
6.5	The two-dimensional and three-dimensional limits	187
6.6	Excitons in single quantum wells	191
6.7	Excitons in multiple quantum wells	194

6.8	Stark ladders	196
6.9	Self-consistent effects	198
6.10	Spontaneous symmetry breaking	199
6.11	2s exciton	200
7	Strained quantum wells, V. D. Jovanović	203
7.1	Stress and strain in bulk crystals	203
7.2	Strain in quantum wells	207
7.3	Strain balancing	210
7.4	Effect on the band profile of quantum wells	213
7.5	The piezoelectric effect	215
7.6	Induced piezoelectric fields in quantum wells	218
7.7	Effect of piezoelectric fields on quantum wells	220
8	Simple models of quantum wires and dots	225
8.1	Further confinement	225
8.2	Schrödinger's equation in quantum wires	228
8.3	Infinitely deep rectangular wires	229
8.4	Simple approximation to a finite rectangular wire	232
8.5	Circular cross-section wire	236
8.6	Quantum boxes	239
8.7	Spherical quantum dots	240
8.8	Non-zero angular momentum states	243
8.9	Approaches to pyramidal dots	244
8.10	Matrix approaches	245
8.11	Finite difference expansions	246
8.12	Density of states	247
9	Quantum dots, M. Califano	251
9.1	0-dimensional systems and their experimental realization	251
9.2	Cuboidal dots	254
9.3	Dots of arbitrary shape	254
9.4	Application to real problems	264
9.5	A more complex model is not always a better model	271
10	Carrier scattering	273
10.1	Fermi's Golden Rule	273
10.2	Phonons	273
10.3	Longitudinal optic phonon scattering of bulk carriers	276

10.4	LO phonon scattering of two-dimensional carriers	284
10.5	Application to conduction subbands	295
10.6	Averaging over carrier distributions	298
10.7	Ratio of emission to absorption	299
10.8	Screening of the LO phonon interaction	301
10.9	Acoustic deformation potential scattering	301
10.10	Application to conduction subbands	307
10.11	Optical deformation potential scattering	309
10.12	Confined and interface phonon modes	311
10.13	Carrier-carrier scattering	312
10.14	Addition of screening	319
10.15	Averaging over an initial state population	320
10.16	Intrasubband versus intersubband	323
10.17	Thermalized distributions	325
10.18	Auger-type intersubband processes	325
10.19	Asymmetric intrasubband processes	327
10.20	Empirical relationships	327
10.21	Carrier-photon scattering	328
10.22	Carrier scattering in quantum wires and dots	334
11	Electron transport	335
11.1	Introduction	335
11.2	Mid-infrared quantum cascade lasers	336
11.3	Realistic quantum cascade laser	340
11.4	Rate equations	342
11.5	Self-consistent solution of the rate equations	344
11.6	Calculation of the current density	346
11.7	Phonon and carrier-carrier scattering transport	346
11.8	Electron temperature	347
11.9	Calculation of the gain	351
11.10	QCLs, QWIPs, QDIPs and other methods	352
12	Optical properties of quantum wells, D. Indjin	355
12.1	Intersubband absorption in quantum wells	355
12.2	Bound-bound transitions	360
12.3	Bound-free transitions	361
12.4	Fermi level	363
12.5	Rectangular quantum well	364
12.6	Intersubband optical non-linearities	371
12.7	Electric polarization	372

12.8	Intersubband second harmonic generation	373
12.9	Maximization of resonant susceptibility	375
13	Optical waveguides, C. A. Evans	381
13.1	Introduction to optical waveguides	381
13.2	Optical waveguide analysis	383
13.3	Optical properties of materials	391
13.4	Application to waveguides of laser devices	399
14	Multiband envelope function (k.p) method, Z. Ikonić	407
14.1	Symmetry, basis states and band structure	407
14.2	Valence band structure and the 6×6 Hamiltonian	409
14.3	4×4 valence band Hamiltonian	412
14.4	Complex band structure	413
14.5	Block-diagonalization of the Hamiltonian	414
14.6	The valence band in strained cubic semiconductors	416
14.7	Hole subbands in heterostructures	418
14.8	Valence band offset	420
14.9	The layer (transfer matrix) method	422
14.10	Quantum well subbands	426
14.11	The influence of strain	427
14.12	Strained quantum well subbands	428
14.13	Direct numerical methods	428
15	Empirical pseudo-potential theory	431
15.1	Principles and approximations	431
15.2	Elemental band structure calculation	432
15.3	Spin-orbit coupling	440
15.4	Compound semiconductors	442
15.5	Charge densities	445
15.6	Calculating the effective mass	448
15.7	Alloys	448
15.8	Atomic form factors	450
15.9	Generalization to a large basis	450
15.10	Spin-orbit coupling within the large basis approach	453
15.11	Computational implementation	455
15.12	Deducing the parameters and application	456
15.13	Isoelectronic impurities in bulk	459
15.14	The electronic structure around point defects	464

16 Microscopic electronic properties of heterostructures	467
16.1 The superlattice unit cell	467
16.2 Application of large basis method to superlattices	471
16.3 Comparison with envelope function approximation	474
16.4 In-plane dispersion	476
16.5 <i>Interface coordination</i>	477
16.6 Strain-layered superlattices	478
16.7 The superlattice as a perturbation	479
16.8 Application to GaAs/AlAs superlattices	484
16.9 Inclusion of remote bands	486
16.10 The valence band	487
16.11 Computational effort	487
16.12 Superlattice dispersion and the interminiband laser	489
16.13 Addition of electric field	490
17 Application to quantum wires and dots	495
17.1 Recent progress	495
17.2 The quantum-wire unit cell	496
17.3 Confined states	499
17.4 V-grooved quantum wires	499
17.5 Along-axis dispersion	500
17.6 Tiny quantum dots	501
17.7 Pyramidal quantum dots	503
17.8 Transport through dot arrays	503
17.9 Anti-wires and anti-dots	506
Concluding remarks	507
Appendix A: Materials parameters	509
References	511
Topic index	533